



SHENZHEN YANGJING MICROELECTRONICS CO.,LTD

TO-252 Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

TO-252

FEATURES

- Low speed switching

MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units	1. BASE
V_{CBO}	Collector-Base Voltage	-40	V	2. COLLECTOR
V_{CEO}	Collector-Emitter Voltage	-30	V	3. EMITTER
V_{EBO}	Emitter-Base Voltage	-6	V	
I_C	Collector Current -Continuous	-3	A	
P_C	Collector Power Dissipation	1.25	W	
T_J	Junction Temperature	150		
T_{stg}	Storage Temperature	-55-150		

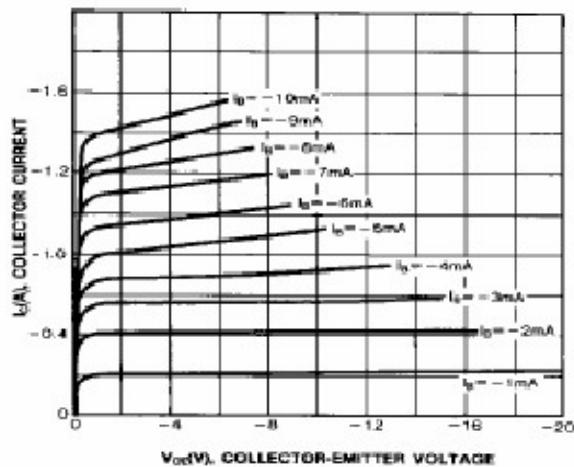
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C= -10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E= -100\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-1		μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V, I_B=0$		-10		μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$		-1		μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C= -1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B= -0.2A$		-0.5		V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B= -0.2A$		-1.5		V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.1A$ $f = 10MHz$	50	80		MHz

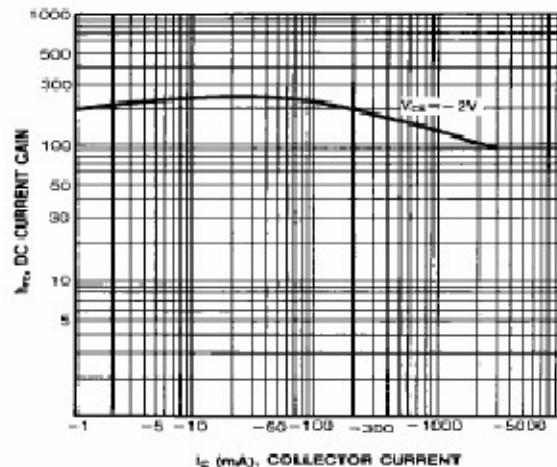
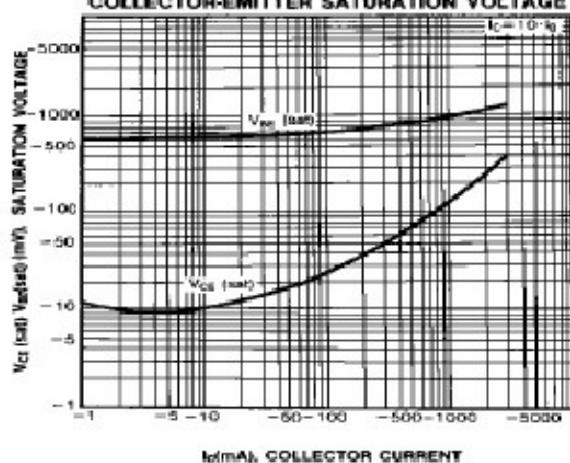
CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

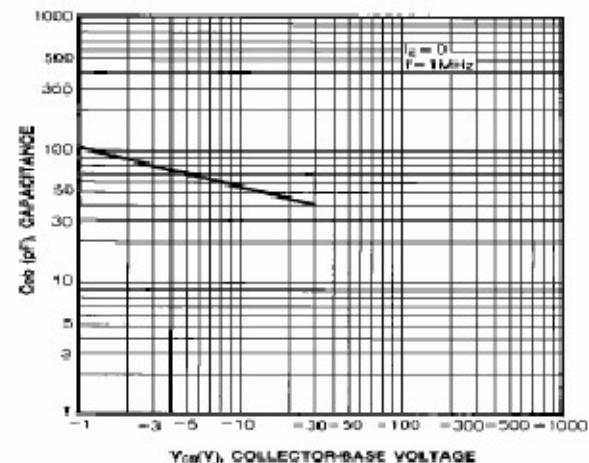
STATIC CHARACTERISTIC



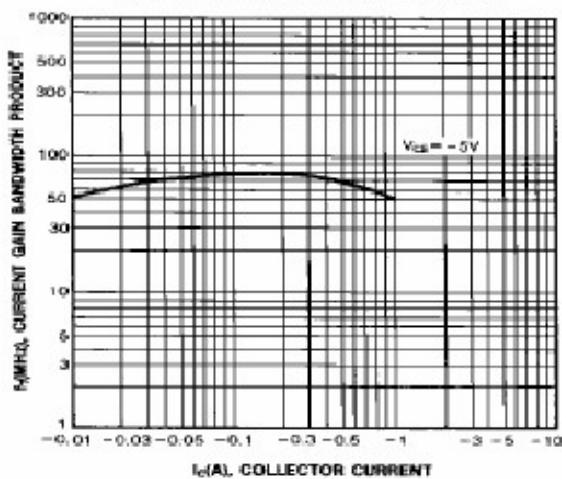
DC CURRENT GAIN

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

COLLECTOR OUTPUT CAPACITANCE



CURRENT GAIN-BANDWIDTH PRODUCT



SAFE OPERATING AREA

